TOSHIBA Transistor Silicon PNP Triple Diffused Type

2SA949

Driver-Stage Audio Amplifier Applications High-Voltage Switching Applications

• High breakdown voltage: $V_{\rm CEO} = -150 \text{ V}$

• Low output capacitance: $C_{ob} = 5.0 pF (max)$

• High transition frequency: fT = 120 MHz (typ.)

Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-150	V
Collector-emitter voltage	V _{CEO}	-150	V
Emitter-base voltage	V _{EBO}	-5	V
Collector current	I _C	-50	mA
Base current	Ι _Β	5	mA
Collector power dissipation	PC	800	mW
Junction temperature	Tj	150	°C
Storage temperature range	T _{stg}	−55 to 150	°C

1. EMITTER 2. COLLECTOR 3. BASE JEDEC TO-92MOD JEITA — TOSHIBA 2-5J1A

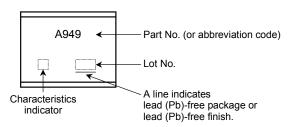
Weight: 0.36 g (typ.)

Electrical Characteristics (Ta = 25°C)

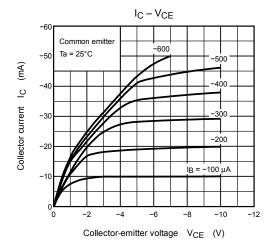
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	V _{CB} = −150 V, I _E = 0	_	_	-0.1	μΑ
Emitter cut-off current	I _{EBO}	$V_{EB} = -5 \text{ V}, I_{C} = 0$	_	_	-0.1	μA
DC current gain	h _{FE} (Note)	V _{CE} = -5 V, I _C = -10 mA	70	_	240	
Collector-emitter saturation voltage	V _{CE (sat)}	I _C = -10 mA, I _B = -1 mA	_	_	-0.8	V
Base-emitter voltage	V _{BE}	$V_{CE} = -5 \text{ V, } I_{C} = -30 \text{ mA}$	_	_	-0.9	V
Transition frequency	f _T	$V_{CE} = -30 \text{ V}, I_{C} = -10 \text{ mA}$	_	120	_	MHz
Collector output capacitance	C _{ob}	V _{CB} = −10 V, I _E = 0, f = 1 MHz	_	4.0	5.0	pF

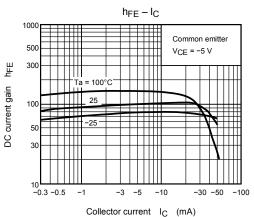
Note: $h_{\mbox{\scriptsize FE}}$ classification $\,$ O: 70 to 140, Y: 120 to 240

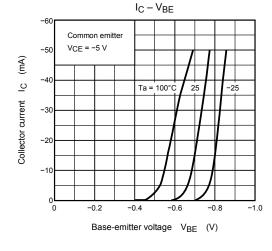
Marking

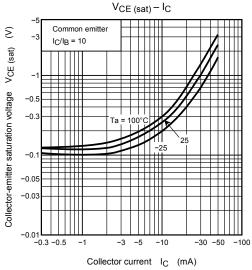


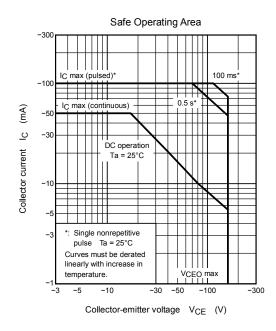
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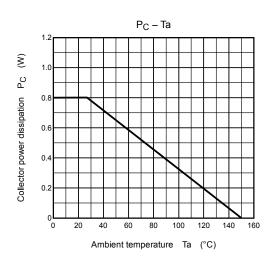












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